

## **P15A**

### **Highly sensitive Hall Effect sensor**

Advanced Hall Sensors Ltd (AHS) specialises in the design and manufacture of semiconductor sensors using the technique of Molecular Beam Epitaxy (MBE), which provides excellent uniformity and reproducibility. P15A Hall Sensor is outstanding for its High sensitivity and its low temperature coefficients. The P15A Hall Sensor is fabricated from AlGaAs/InGaAs/GaAs-2DEG (Two-dimensional electron gas) heterojunction semiconductors. Due to its wide band-gap material and high mobility, this sensor provides numerous advantages over existing Silicon technology.

#### **Features and benefits**

- High Sensitivity (850V/AT)
- Low current requirement
- Very low power consumption
- Extended operating temperature range
- Small linearity error of the Hall voltage
- Plastic miniature package for through slot and SOT-143 surface mounting

#### **Potential applications**

- Magnetic field measurement
- Low temperature applications
- Current and power measurements
- Control of brushless DC motors
- Micro switches
- Position sensing
- Speed and RPM sensing

**Table 1. Absolute maximum ratings**

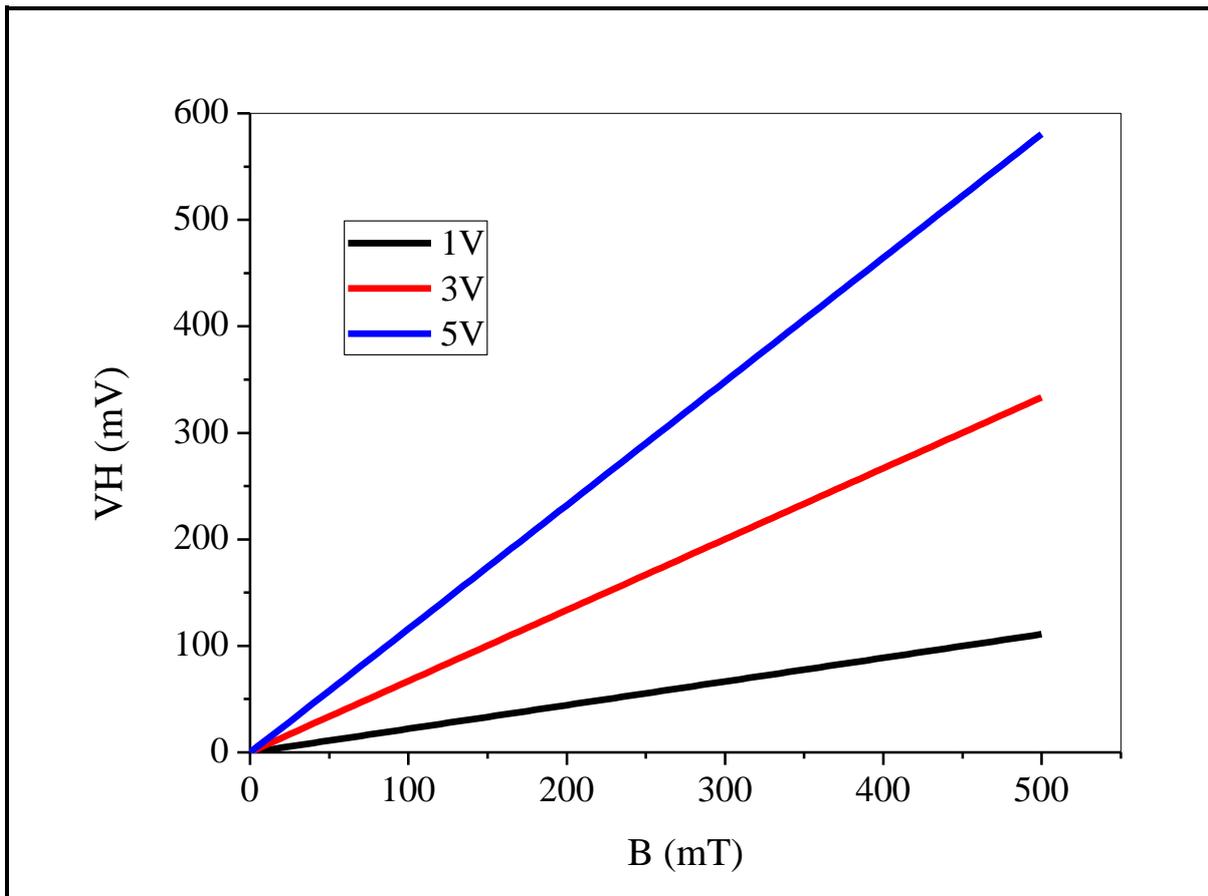
Parameter	Symbol	Rating	Unit
Control Voltage	V <sub>C</sub>	5	V
Control Current	I <sub>C</sub>	1.4	mA
Power Dissipation	P <sub>D</sub>	7	mW
Operating Temperature	T <sub>OP</sub>	-100 to +200	°C
Storage temperature	T <sub>S</sub>	-100 to +200	°C
Soldering temperature	T <sub>SOL</sub>	260	°C

**Table 2. Electrical characteristics**

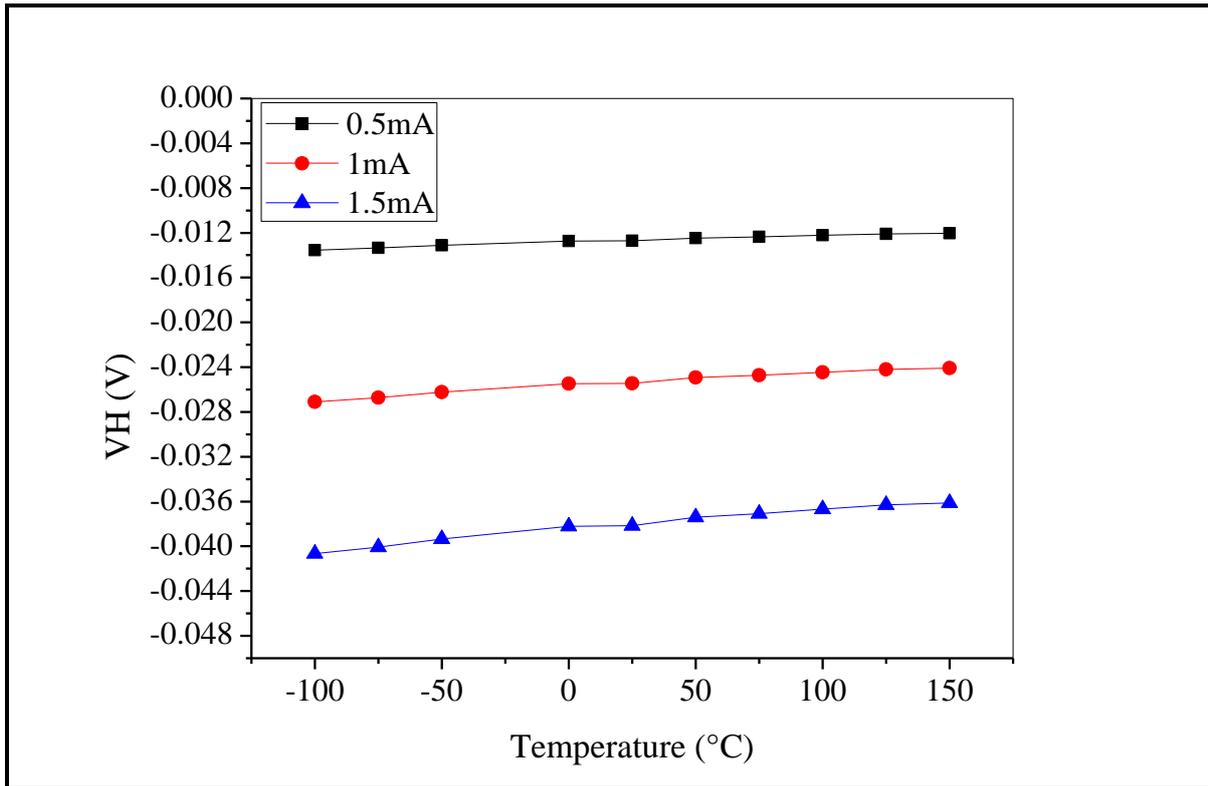
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Output Hall Voltage	V <sub>H</sub>	I <sub>C</sub> =1mA, B=100mT	75	85	95	mV
Residual Ratio <sup>*1</sup>	V <sub>HO</sub> /V <sub>H</sub>	I <sub>C</sub> =1mA	-10		+10	%
Residual Ratio	V <sub>HO</sub> /V <sub>H</sub>	I <sub>C</sub> =0.5mA	-5		+5	%
Input Resistance	R <sub>IN</sub>	I <sub>C</sub> =0.5mA, B=0mT	3.1	3.5	4.1	kΩ
Output Resistance	R <sub>OUT</sub>	I <sub>C</sub> =0.5mA, B=0mT	3.1	3.5	4.1	kΩ
Temperature coefficient of Hall Voltage <sup>*2</sup>	α	I <sub>C</sub> =1mA, B=100mT (T <sub>1</sub> =-100°C, T <sub>2</sub> =150°C)	-0.05	-0.08	-0.13	%/°C
Temperature coefficient of Input Resistance <sup>*3</sup>	β	I <sub>C</sub> =1mA, B=0mT (T <sub>1</sub> =-100°C, T <sub>2</sub> =150°C)	-----	0.3	0.4	%/°C
Linearity of Hall Voltage <sup>*4</sup>	γ	I <sub>C</sub> =1mA, B <sub>1</sub> =60mT, B <sub>2</sub> =500mT	-----	1	1.5	%

**Notes:**

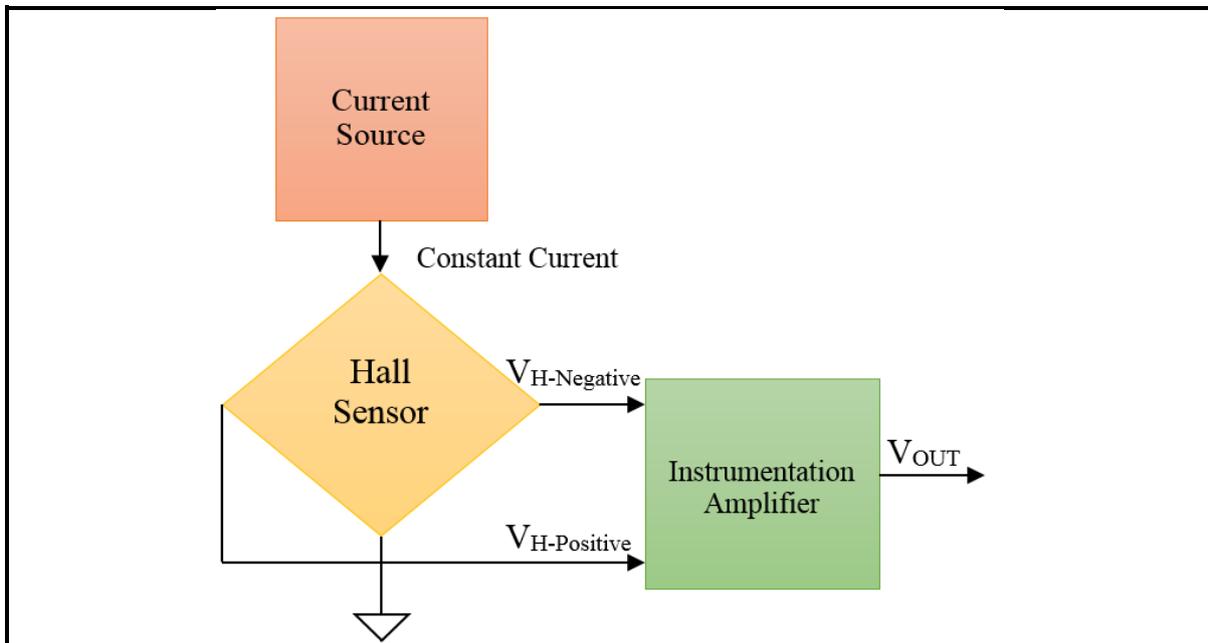
1. $Residual\_Ratio = \frac{V_{HO}(B=0mT)}{V_H(B=100mT)}$	2. $\alpha = \frac{1}{V_H(T_1)} \times \frac{V_H(T_2) - V_H(T_1)}{T_2 - T_1} \times 100$
3. $\beta = \frac{1}{R_{IN}(T_1)} \times \frac{R_{IN}(T_2) - R_{IN}(T_1)}{T_2 - T_1} \times 100$	4. $\gamma = \frac{K_H(B_2) - K_H(B_1)}{\frac{1}{2}[K_H(B_1) + K_H(B_2)]} \times 100$
<p><math>V_{HO}</math>: Offset voltage  <math>B</math>: Magnetic flux density  <math>T_1, T_2</math>: Ambient Temperature  <math>K_H</math>: Current sensitivity</p>	
$K_H = \frac{V_H}{IB}$	



**Figure 1. Output Hall Voltage versus Magnetic field at inputs of 1V, 3V and 5V across the Hall sensor.**



**Figure 2. Output Hall Voltage versus Temperature at input bias currents of 0.5mA, 1mA and 1.5mA across the Hall sensor and at 30mT magnetic field.**



**Figure 3. Recommended circuit.**

<お問い合わせは> 株式会社 セスナ  
 東京都港区赤坂4-1-1  
 SHIMA赤坂ビル (〒107-0052)  
 TEL 03-6234-4347  
 sales@sesna.net  
 https://sesna.net/

**Contact us:**

**Email:** sales@ahsltd.com

**Phone:** +44 161 873 7334

**Address:** Advanced Hall Sensors Ltd, Unit C3, Broadoak Business Park, Ashburton Road  
 West Trafford Park Manchester, M17 1RW

Outline drawings (unit: mm)

